

| L Number | Hits    | Search Text  | DB  | Time stamp       |
|----------|---------|--|---|------------------|
| 1        | 9       | ma-ching-tien-.in. chen-tsung-chuan-.in.<br>hsu-shew-tsu-.in.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:49 |
| 2        | 452476  | resist photoresist photo-resist  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:50 |
| 3        | 339939  | photosensitive photo-sensitive (sensitive<br>near (photo light energy radiation))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:50 |
| 4        | 9231    | duv! (deep adj2 (uv ultraviolet ultra-violet<br>ultra adj violet))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:50 |
| 5        | 116798  | krf arf f2 "f.sub.2"   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:50 |
| 6        | 12147   | ("157" "193" "248") near (nm! nanometer<br>nano-meter nano adj meter)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:51 |
| 7        | 275665  | (oxide dioxide) near (layer film coating)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:51 |
| 8        | 21899   | etchstop etch-stop etch adj stop hardmask<br>hard-mask hard adj mask   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:51 |
| 9        | 1866544 | si silicon si-contain\$3 silicon-contain\$3  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:51 |
| 10       | 232413  | (silicon adj (nitride oxynitride oxy-nitride<br>oxy adj nitride carbide)) "si.sub.3 n.sub.4"<br>sion sic   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:51 |
| 11       | 7658    | (430/311,313,314,317,327,328,330.ccls.<br>328/694.ccls.)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:51 |
| 13       | 68211   | aspect adj ratio   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:52 |
| 14       | 2549112 | via contact adj hole   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:53 |
| 15       | 9000    | (etchstop etch-stop etch adj stop hardmask<br>hard-mask hard adj mask ) with ((si silicon<br>si-contain\$3 silicon-contain\$3 ) ((silicon<br>adj (nitride oxynitride oxy-nitride oxy adj<br>nitride carbide)) "si.sub.3 n.sub.4" sion<br>sic ))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:54 |
| 16       | 7988    | ((resist photoresist photo-resist )<br>(photosensitive photo-sensitive (sensitive<br>near (photo light energy radiation)) )) with<br>((duv! (deep adj2 (uv ultraviolet<br>ultra-violet ultra adj violet)) ) (krf arf<br>f2 "f.sub.2" ) (("157" "193" "248") near<br>(nm! nanometer nano-meter nano adj meter) )) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 11:54 |
| 20       | 66778   | (cur\$3 near2 (uv ultraviolet ultra-violet<br>ultra adj violet (duv! (deep adj2 (uv<br>ultraviolet ultra-violet ultra adj violet))<br>) light radiation)) photo-cur\$3 photocur\$3   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:02 |

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| 21 | 2396 | ((resist photoresist photo-resist )<br>(photosensitive photo-sensitive (sensitive<br>near (photo light energy radiation)) ))<br>near4 ((cur\$3 near2 (uv ultraviolet<br>ultra-violet ultra adj violet (duv! (deep<br>adj2 (uv ultraviolet ultra-violet ultra adj<br>violet)) ) light radiation)) photo-cur\$3<br>photocur\$3)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:03 |
| 22 | 4    | ((resist photoresist photo-resist )<br>(photosensitive photo-sensitive (sensitive<br>near (photo light energy radiation)) ))<br>near4 ((cur\$3 near2 (uv ultraviolet<br>ultra-violet ultra adj violet (duv! (deep<br>adj2 (uv ultraviolet ultra-violet ultra adj<br>violet)) ) light radiation)) photo-cur\$3<br>photocur\$3)) same ((oxide dioxide) near<br>(layer film coating) ) same ((etchstop<br>etch-stop etch adj stop hardmask hard-mask<br>hard adj mask ) with ((si silicon<br>si-contain\$3 silicon-contain\$3 ) ((silicon<br>adj (nitride oxynitride oxy-nitride oxy adj<br>nitride carbide)) "si.sub.3 n.sub.4" sion<br>sic )))             | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:11 |
| 23 | 1051 | ((resist photoresist photo-resist )<br>(photosensitive photo-sensitive (sensitive<br>near (photo light energy radiation)) )) same<br>((oxide dioxide) near (layer film coating) )<br>same ((etchstop etch-stop etch adj stop<br>hardmask hard-mask hard adj mask ) with ((si<br>silicon si-contain\$3 silicon-contain\$3 )<br>((silicon adj (nitride oxynitride<br>oxy-nitride oxy adj nitride carbide))<br>"si.sub.3 n.sub.4" sion sic )))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:12 |
| 24 | 34   | ((resist photoresist photo-resist )<br>(photosensitive photo-sensitive (sensitive<br>near (photo light energy radiation)) )) same<br>((oxide dioxide) near (layer film coating) )<br>same ((etchstop etch-stop etch adj stop<br>hardmask hard-mask hard adj mask ) with ((si<br>silicon si-contain\$3 silicon-contain\$3 )<br>((silicon adj (nitride oxynitride<br>oxy-nitride oxy adj nitride carbide))<br>"si.sub.3 n.sub.4" sion sic )))) and ((duv!<br>(deep adj2 (uv ultraviolet ultra-violet<br>ultra adj violet)) ) (krf arf f2 "f.sub.2" )<br>(("157" "193" "248") near (nm! nanometer<br>nano-meter nano adj meter) )) and (aspect<br>adj ratio) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:20 |
| 25 | 5585 | (aspect adj ratio) with (via contact adj<br>hole)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:21 |
| 27 | 948  | ((aspect adj ratio) with (via contact adj<br>hole)) with ("8" "9" "10" "11" "12" "13"<br>"14" "15" "20")  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:26 |
| 29 | 1734 | ((aspect adj ratio) with (via contact adj<br>hole)) with (least greater more between<br>range)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:27 |
| 30 | 1    | ((aspect adj ratio) with (via contact adj<br>hole)) with (least greater more between<br>range)) same ((resist photoresist<br>photo-resist ) (photosensitive<br>photo-sensitive (sensitive near (photo light<br>energy radiation)) )) same ((etchstop<br>etch-stop etch adj stop hardmask hard-mask<br>hard adj mask ) with ((si silicon<br>si-contain\$3 silicon-contain\$3 ) ((silicon<br>adj (nitride oxynitride oxy-nitride oxy adj<br>nitride carbide)) "si.sub.3 n.sub.4" sion<br>sic )))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:28 |

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| 32 | 9   | ((aspect adj ratio) with (via contact adj hole)) with (least greater more between range)) same ((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) same (etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask )  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:28 |
| 31 | 108 | ((aspect adj ratio) with (via contact adj hole)) with (least greater more between range)) and ((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) and ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon si-contain\$3 silicon-contain\$3 ) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic )))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:31 |
| 33 | 18  | ((aspect adj ratio) with (via contact adj hole)) with (least greater more between range)) and ((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) and ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon si-contain\$3 silicon-contain\$3 ) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic ))) and ((duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet)) ) (("157" "193" "248") near (nm! nanometer nano-meter nano adj meter) ))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:36 |
| 34 | 90  | ((aspect adj ratio) with (via contact adj hole)) with (least greater more between range)) and ((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) and ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon si-contain\$3 silicon-contain\$3 ) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic )))) not (((aspect adj ratio) with (via contact adj hole)) with (least greater more between range)) and ((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) and ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon si-contain\$3 silicon-contain\$3 ) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic ))) and ((duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet)) ) (("157" "193" "248") near (nm! nanometer nano-meter nano adj meter) )))) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT | 2004/07/20 12:36 |